TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process) Silicon PNP Epitaxial Type (PCT Process)

# HN1B04FU

## Audio Frequency General Purpose Amplifier Applications

Q1:High voltage and high current

 $: V_{CEO} = 50V, I_{C} = 150mA (max)$ 

• High h<sub>FE</sub>:  $h_{FE} = 120 \sim 400$ 

• Excellent hfe linearity

 $: h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (typ.)}$ 

#### Q2:

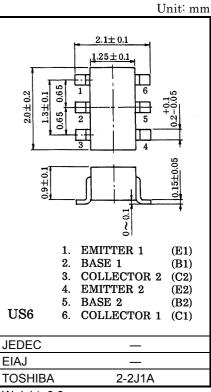
• High voltage and high current

 $: V_{CEO} = -50V, I_C = -150 \text{mA (max)}$ 

• High  $h_{FE}$ :  $h_{FE} = 120 \sim 400$ 

Excellent hfe linearity

:  $h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 \text{ (typ.)}$ 

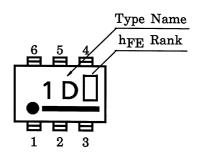


Weight: 6.8mg

## Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	60	٧
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	٧
Collector current	I <sub>C</sub>	150	mA
Base current	Ι <sub>Β</sub>	30	mA

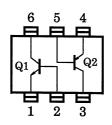
#### Marking



# Q2 Maximum Ratings (Ta = 25°C)

# **Equivalent Circuit (Top View)**

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-150	mA
Base current	Ι <sub>Β</sub>	-30	mA



# Q1,Q2 Common Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> *	200	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

<sup>\*</sup> Total rating

## Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0	_	_	0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	_	$V_{EB} = 5V, I_{C} = 0$	1	1	0.1	μΑ
DC current gain	h <sub>FE (Note)</sub>	_	V <sub>CE</sub> = 6V, I <sub>C</sub> = 2mA	120	-	400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA	-	0.1	0.25	٧
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1mA	_	150	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	$V_{CB} = 10V$ , $I_E = 0$ , $f = 1MHz$	-	2	_	pF

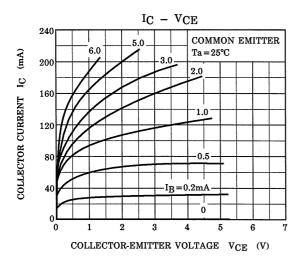
## **Q2 Electrical Characteristics (Ta = 25°C)**

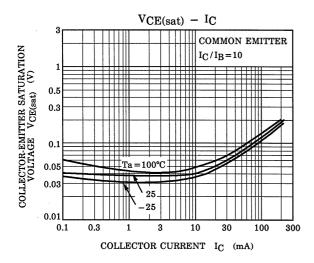
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0	_	_	-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	_	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0	_	_	-0.1	μA
DC current gain	h <sub>FE (Note)</sub>	_	$V_{CE} = -6V, I_{C} = -2mA$	120	-	400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA	_	-0.1	-0.3	٧
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = −10V, I <sub>C</sub> = −1mA	_	120	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	$V_{CB} = -10V, I_{E} = 0,$ f = 1MHz	_	4	_	pF

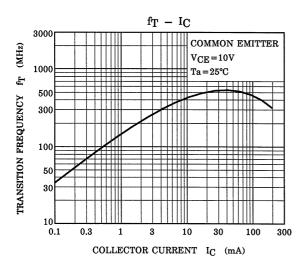
Note: hfe Classification Y (Y): 120~240, GR (G): 200~400

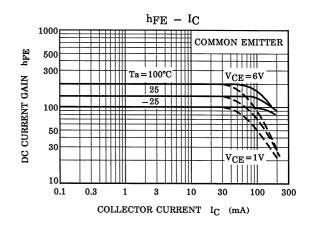
( ) Marking Symbol

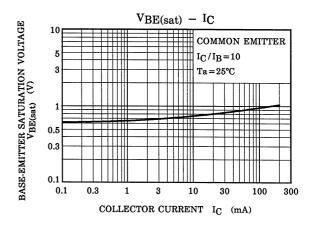
#### Q1 (NPN transistor)

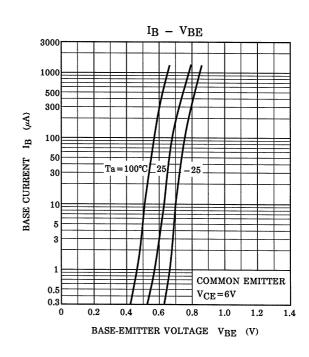




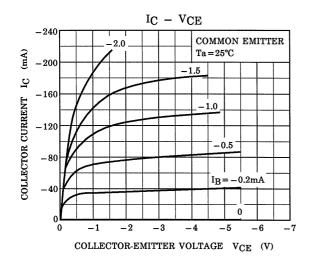


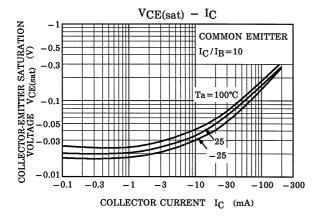


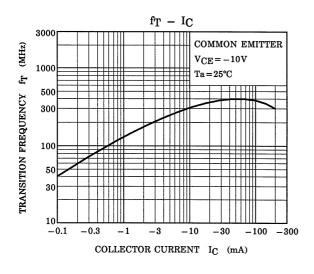


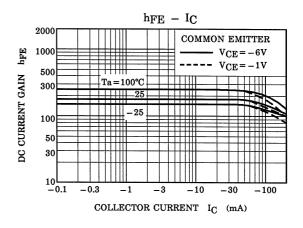


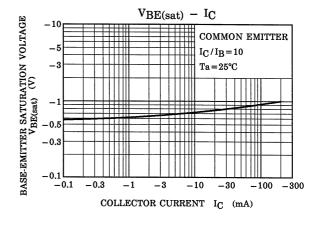
## Q2 (PNP transistor)

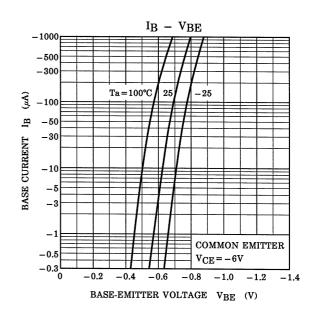




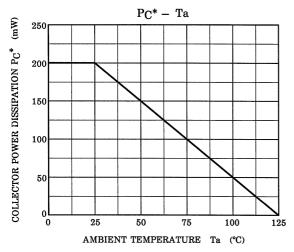








# (Q1, Q2 Common)



\*: Total Rating

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